Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- · Logic level compatible
- · Very fast switching
- Trench MOSFET technology
- · Enhanced power dissipation capability of 1115 mW

3. Applications

- · Relay driver
- · High-speed line driver
- · Low-side load switch
- · Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	-	30	V
V_{GS}	gate-source voltage			-20	-	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C; t ≤ 5 s	[1]	-	-	5.1	Α
Static characte	Static characteristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 4.1 \text{ A}; T_j = 25 \text{ °C}$		-	35	42	mΩ

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	3	D I
2	S	source		
3	D	drain		G 4
			1 2	\$ 017aaa253
			TO-236AB (SOT23)	

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMV45EN2	TO-236AB	plastic surface-mounted package; 3 leads	SOT23			

7. Marking

Table 4. Marking codes

Type number	Marking code ^[1]
PMV45EN2	%K9

[1] % = placeholder for manufacturing site code

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	30	V
V _{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C; t ≤ 5 s	[1]	-	5.1	Α
		V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	4.1	Α
		V _{GS} = 10 V; T _{amb} = 100 °C	[1]	-	2.6	Α
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	16	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	510	mW
			[1]	-	1115	mW
		T _{sp} = 25 °C		-	5000	mW
T _j	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain	diode					
I _S	source current	T _{amb} = 25 °C	[1]	-	1	Α

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².
- [2] Device mounted on an FR4 Printed Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

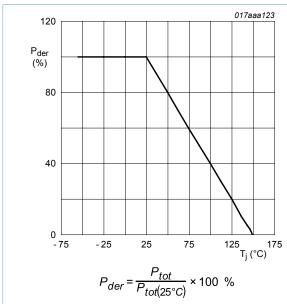


Fig. 1. Normalized total power dissipation as a function of junction temperature

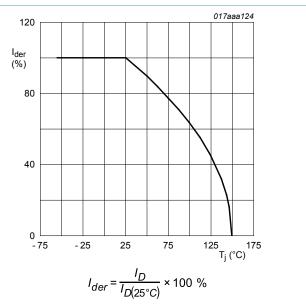
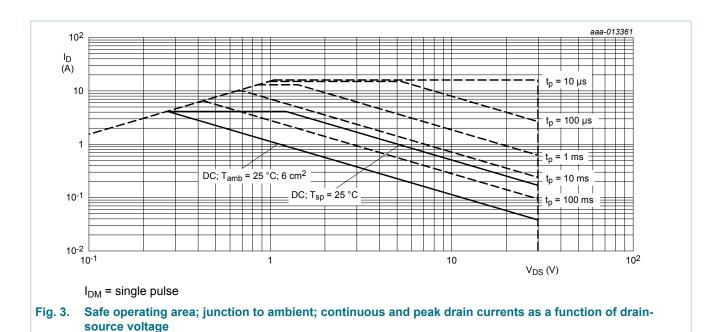


Fig. 2. Normalized continuous drain current as a function of junction temperature

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance	III II EE ali	[1]	-	209	246	K/W
	from junction to ambient		[2]	-	95	112	K/W
	ambione	in free air; t ≤ 5 s	[2]	-	62	73	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	20	25	K/W

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².

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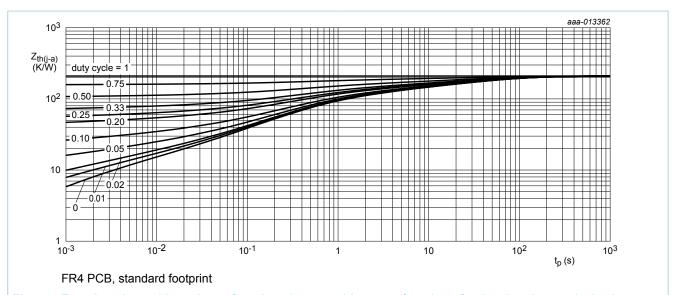


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

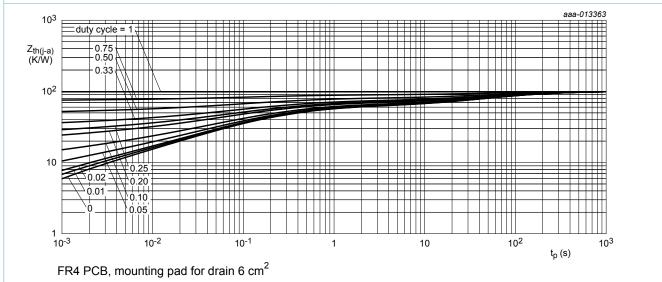


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					,
V _{(BR)DSS}	drain-source breakdown voltage	I_D = 250 μ A; V_{GS} = 0 V; T_j = 25 °C	30	-	-	V
V_{GSth}	gate-source threshold voltage	I_D = 250 μ A; V_{DS} = V_{GS} ; T_j = 25 °C	1	1.5	2	V
I _{DSS}	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-	1	μΑ
I _{GSS}	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-	100	nA
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-100	nA
R _{DSon}	drain-source on-state	V _{GS} = 10 V; I _D = 4.1 A; T _j = 25 °C	-	35	42	mΩ
resista	resistance	V _{GS} = 10 V; I _D = 4.1 A; T _j = 150 °C	-	55	66	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 3.6 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	43	54	mΩ
9 _{fs}	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 2 \text{ A}; T_j = 25 \text{ °C}$	-	13	-	S
R_{G}	gate resistance	T _j = 25 °C; f = 1 MHz	-	2.3	-	Ω
Dynamic ch	naracteristics		,			
Q _{G(tot)}	total gate charge	V_{DS} = 15 V; I_{D} = 3.2 A; V_{GS} = 10 V;	-	3.6	6.3	nC
Q_{GS}	gate-source charge	T _j = 25 °C	-	0.5	-	nC
Q_{GD}	gate-drain charge		-	0.4	-	nC
C _{iss}	input capacitance	V _{DS} = 15 V; f = 1 MHz; V _{GS} = 0 V;	-	209	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	50	-	pF
C _{rss}	reverse transfer capacitance		-	17	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = 15 V; I _D = 3.2 A; V _{GS} = 10 V;	-	3	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	12	-	ns
t _{d(off)}	turn-off delay time		-	11	-	ns
t _f	fall time		-	2	-	ns
Source-dra	in diode		1			,
V_{SD}	source-drain voltage	I _S = 1 A; V _{GS} = 0 V; T _i = 25 °C	-	0.8	1.2	V

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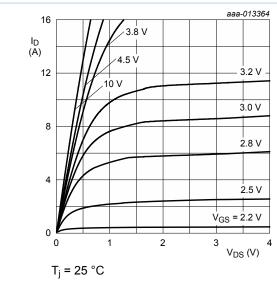


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

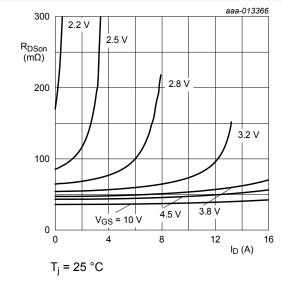


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

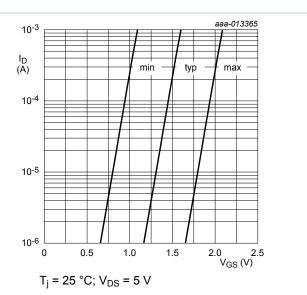


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

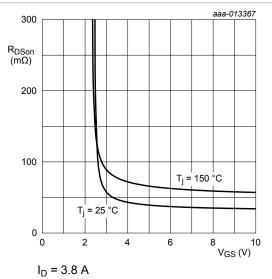


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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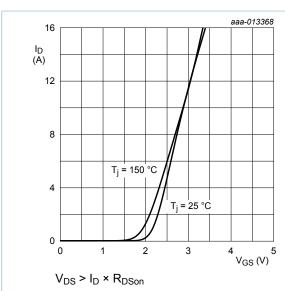


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

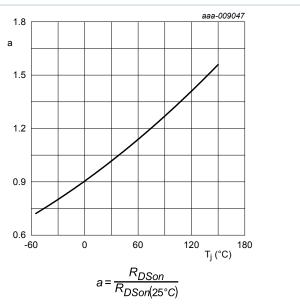


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

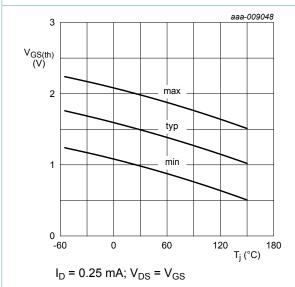


Fig. 12. Gate-source threshold voltage as a function of junction temperature

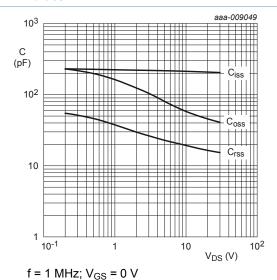


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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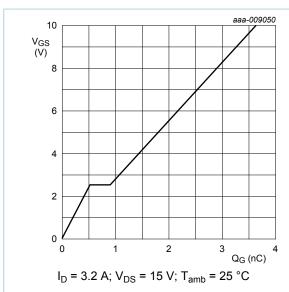


Fig. 14. Gate-source voltage as a function of gate charge; typical values

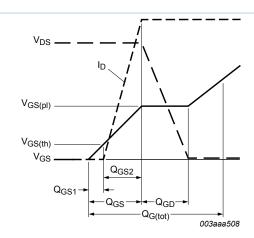


Fig. 15. MOSFET transistor: Gate charge waveform definitions

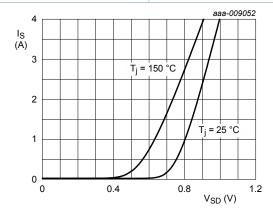
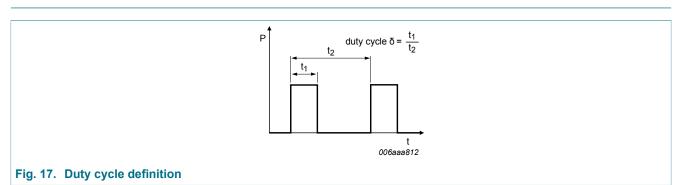


Fig. 16. Source current as a function of source-drain voltage; typical values

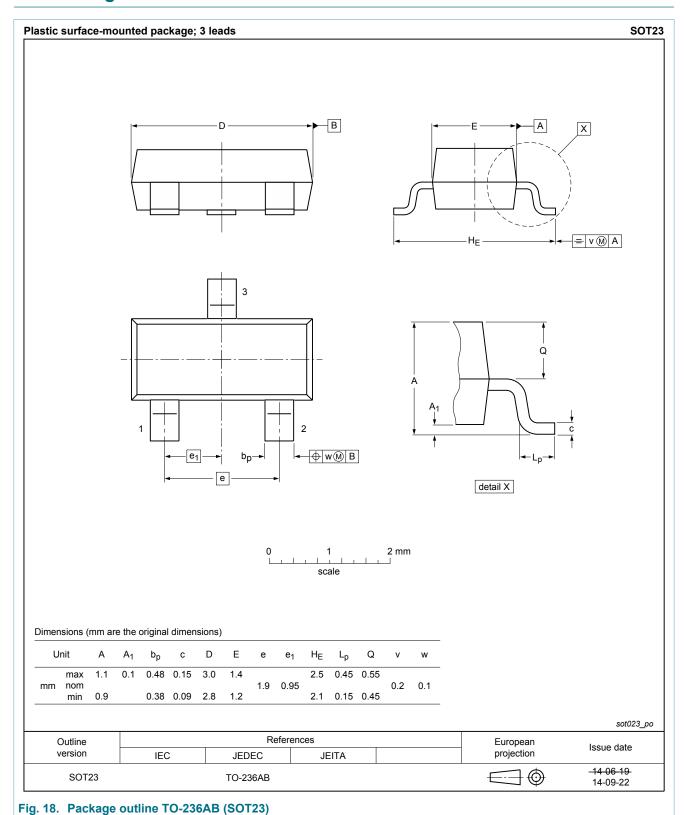
11. Test information

 $V_{GS} = 0 V$



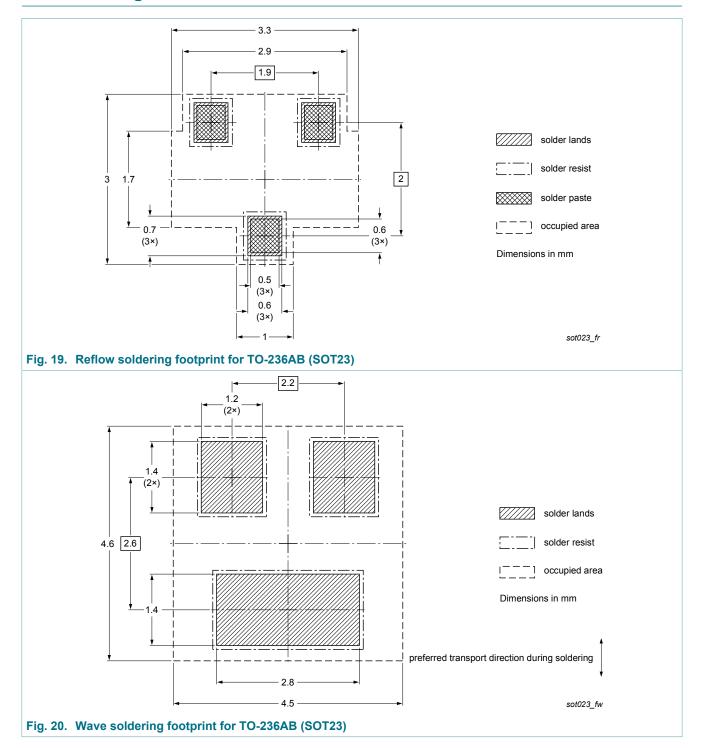
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12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes					
PMV45EN2 v.2	20170110	Product data sheet	-	PMV45EN2 v.1					
Modifications:	Section 10. Characte	Section 10. Characteristics: values for forward transconductance and gate resistance changed							
PMV45EN2 v.1	20140603	Product data sheet	-	-					

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15. Legal information

Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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